

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions of claims in the application.

1. (Currently amended): A semiconductor device comprising:

a first insulating film formed over a semiconductor substrate;

a second insulating film formed over the first insulating film;

an interconnection structure buried in the first insulating film and in the second insulating film;

a plurality of first dummy pattern ~~of patterns formed from~~ a first conducting layer buried in at least a surface side of the first insulating film near the interconnection structure; and

a plurality of second dummy pattern ~~formed of patterns formed from~~ a second conducting layer buried in the second insulating film ~~near the interconnection structure~~ and connected to the plurality of first dummy pattern ~~patterns~~ through ~~[[a]]~~ via ~~portion~~ portions, the plurality of second dummy pattern ~~patterns~~ ~~comprising a plurality of discrete patterns which are being~~ adjacent to each other and disposed at even intervals so as to make a pattern density of elements formed from the second conducting layer substantially uniform in plane.
2. (Currently amended): A semiconductor device according to claim 1, wherein

the interconnection structure includes a first interconnection pattern buried in the first insulating film and formed ~~[[of]]~~ from the first conducting layer, and a second interconnection pattern buried in the second insulating film, formed ~~[[of]]~~ from the second conducting layer and connected to the first interconnection pattern through a via portion.

3. (Cancelled).

4. (Currently amended): A semiconductor device according to claim 1, wherein
~~the via portion through which the second dummy pattern is connected to the first dummy~~
~~pattern is formed in a part of the discrete plurality of second dummy~~ patterns arranged near the
interconnection structure are connected to the first dummy patterns via the via portions.

5. (Currently amended): A semiconductor device according to claim 1, wherein
the plurality of first dummy pattern ~~comprises a plurality of discrete patterns periodically~~
~~formed~~ patterns are adjacent to each other and disposed at even intervals so as to make a pattern
density of elements formed from the first conducting layer substantially uniform in plane.

6. (Original): A semiconductor device according to claim 1, wherein
the first conducting layer and the second conducting layer are formed of a conducting
material mainly based on copper.

7. (Previously presented): A semiconductor device according to claim 1, wherein
the first insulating film and the second insulating film are formed of films based mainly
on different insulating materials with each other.

8. (Original): A semiconductor device according to claim 7, wherein
the first insulating film is mainly formed of a polyallyl ether resin film, and
the second insulating film is mainly formed of a organosilicate glass film.

9. (Original): A semiconductor device according to claim 2, wherein

Amendment Under 37 C.F.R. §1.111
Application No. 10/694,766
Attorney Docket No. 032069

the via portion through which the second interconnection pattern is connected to the first interconnection pattern has a groove-shaped pattern.

10. (Original): A semiconductor device according to claim 1, wherein
the interconnection structure is a guard ring, an inductor or a pad.

11-18. (Cancelled).